

DMP1245UFCL
12V P-CHANNEL ENHANCEMENT MODE MOSFET
Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D max
-12V	29mΩ @ $V_{GS} = -4.5V$	-6.6 A
	45mΩ @ $V_{GS} = -2.5V$	-5.3 A
	60mΩ @ $V_{GS} = -1.8V$	-4.6 A
	100mΩ @ $V_{GS} = -1.5V$	-3.5 A

Application

This device provides a high performance, low $R_{DS(ON)}$ P channel MOSFETs in the thermally and space efficient X1-DFN1616-6 package. The low $R_{DS(ON)}$ of this MOSFET ensures conduction losses are kept making it ideal for use as a:

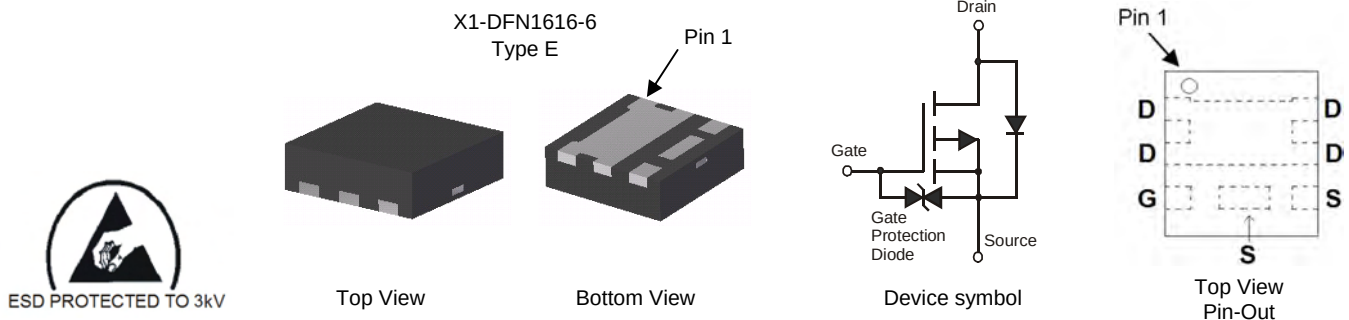
- Battery disconnect switch
- Load switch for power management functions

Features and Benefits

- Typical off board profile of 0.5mm - ideally suited for thin applications
- Low $R_{DS(ON)}$ – minimizes conduction losses
- PCB footprint of 2.56mm²
- 3kV ESD Protected Gate** – protected against human borne ESD
- "Lead-Free", RoHS Compliant (Note 1)
- "Green" Device (Note 2)

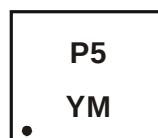
Mechanical Data

- Case: X1-DFN1616-6 Type E
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Lead Free Plating (NiPdAu Finish over Copper leadframe).
- Terminals: Solderable per MIL-STD-202, Method 208
- Weight: 0.04 grams (approximate)


Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMP1245UFCL-7	P5	7	8	3,000

- Notes:
- No purposefully added lead.
 - Diodes Inc's "Green" Policy can be found on our website at <http://www.diodes.com>
 - For packaging details, go to our website at <http://www.diodes.com>

Marking Information


P5 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: X = 2010)
M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-12	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 5)	I _D	-6.6 @T _A = 70°C -5.25	A
Pulsed Drain Current	I _{DM}	-16.67	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P _D	613	mW
(Note 5)		1.7	W
Thermal Resistance, Junction to Ambient (Note 4)	R _{θJA}	204	°C/W
(Note 5)		74	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
4. For a device surface mounted on minimum recommended pad layout, in still air conditions; the device is measured when operating in a steady state condition.
 5. For a device surface mounted on 25mm by 25mm by 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady state condition.

Thermal Characteristics

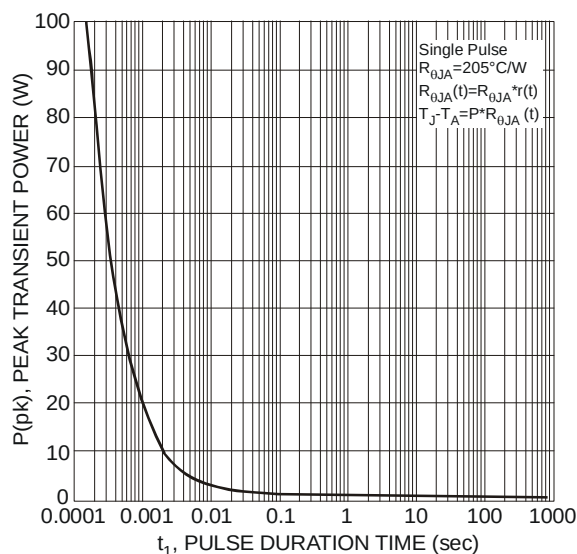


Fig. 1 Single Pulse Maximum Power Dissipation

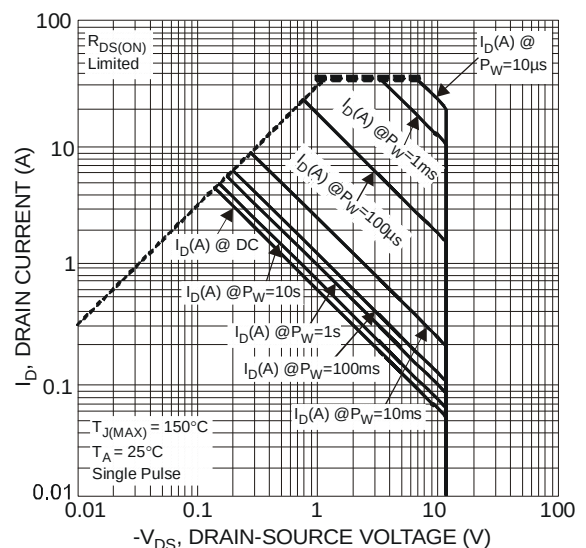
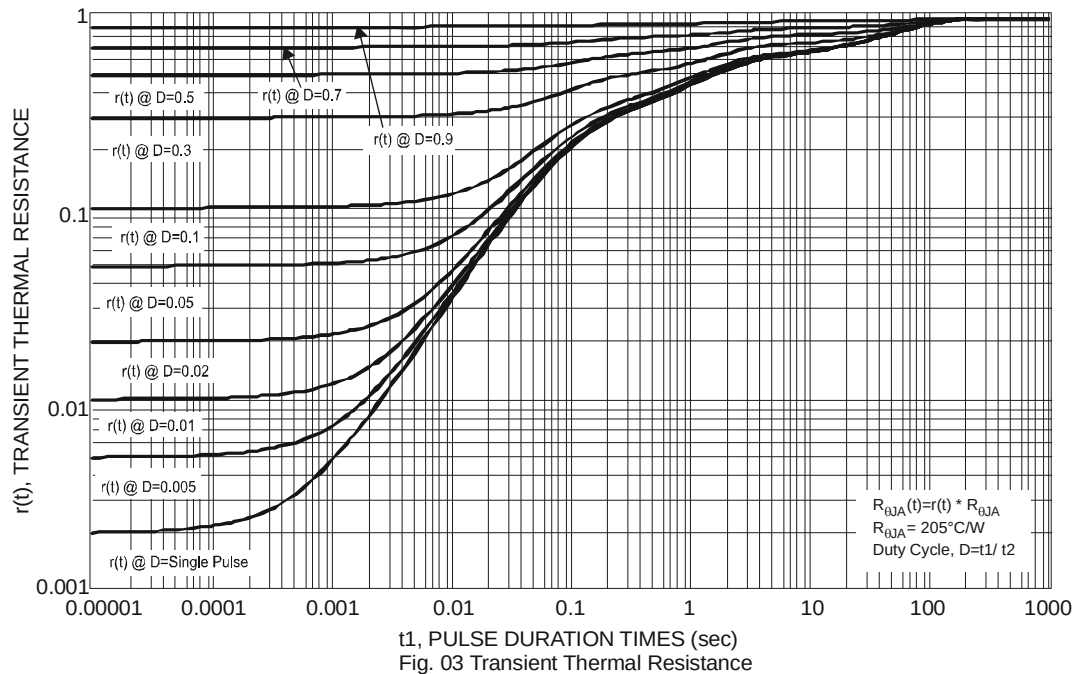


Fig. 2 SOA, Safe Operation Area



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-12	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	—	—	-1	μA	V _{DS} = -12.0V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8.0V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.3	-0.6	-0.95	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	25	29	mΩ	V _{GS} = -4.5V, I _D = -4A
		—	31	45		V _{GS} = -2.5V, I _D = -3.5A
		—	40	60		V _{GS} = -1.8V, I _D = -1A
		—	60	100		V _{GS} = -1.5V, I _D = -0.5A
Forward Transfer Admittance	Y _{fs}	0.4	3	-	S	V _{DS} = -5V, I _D = -2A
Diode Forward Voltage	V _{SD}	-	-	-1.0	V	V _{GS} = 0V, I _D = -2A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	1357.4	-	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	-	499	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	273.6	-	pF	
Gate Resistance	R _g	-	14.26	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	-	16.1	-	nC	V _{GS} = -4.5V I _D = -1A, V _{DS} = -10V
Gate-Source Charge	Q _{gs}	-	26.1	-	nC	
Gate-Drain Charge	Q _{gd}	-	1.71	-	nC	
Turn-On Delay Time	t _{D(on)}	-	20.48	-	ns	V _{GS} = -8V
Turn-On Rise Time	t _r	-	15.2	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	33.11	-	ns	
Turn-Off Fall Time	t _f	-	219.4	-	ns	
		-	217.64	-	ns	V _{GS} = -2.5V, V _{DS} = -10V I _D = -180mA, R _G = 2.0Ω,

Notes: 6. Short duration pulse test used to minimize self-heating effect.
 7. Guaranteed by design. Not subject to production testing.

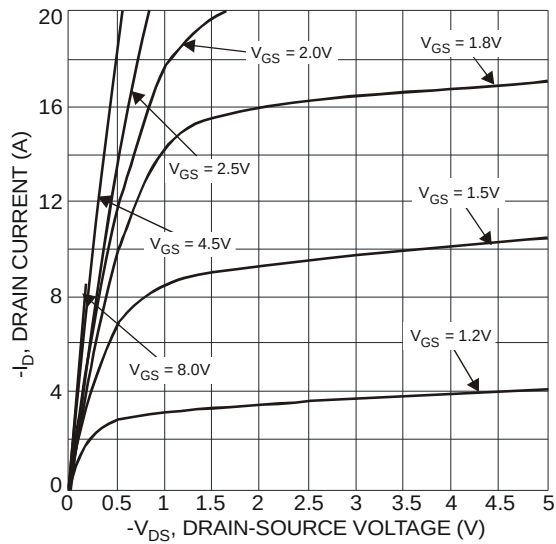


Fig. 4 Typical Output Characteristics

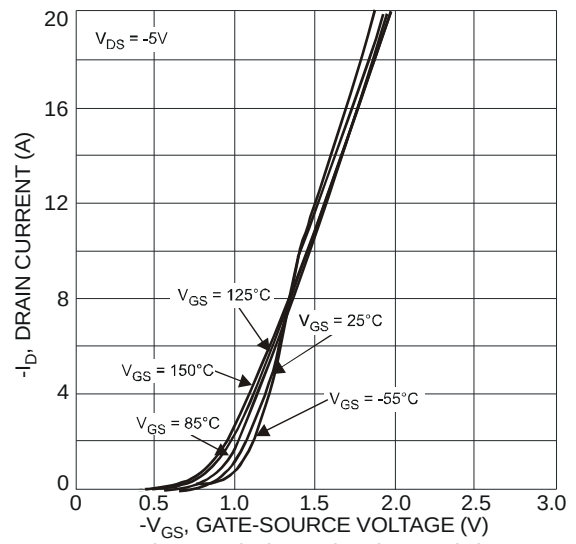


Fig. 5 Typical Transfer Characteristic

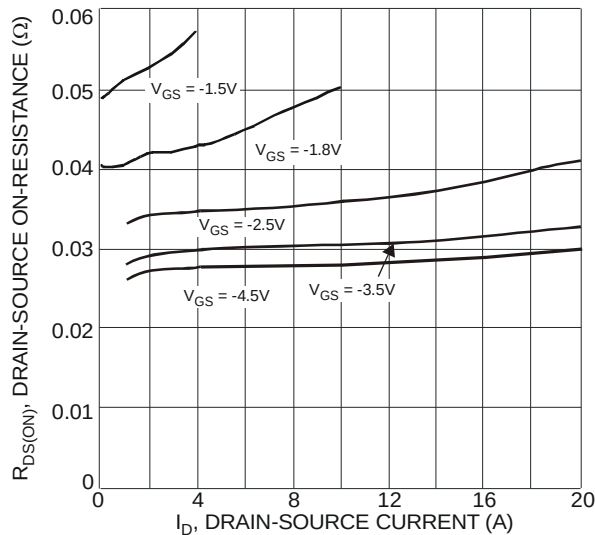


Fig. 6 Typical On-Resistance
vs. Drain Current and Gate Voltage

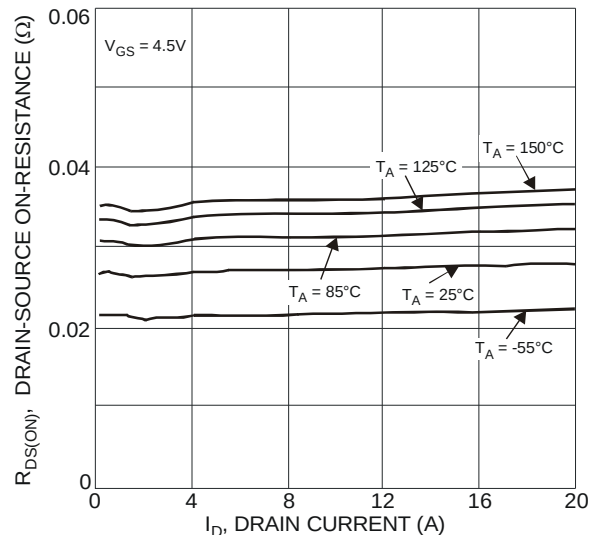


Fig. 7 Typical On-Resistance
vs. Drain Current and Temperature

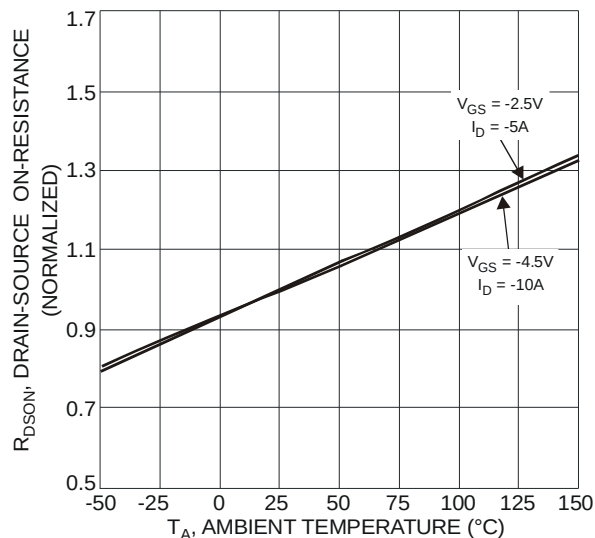


Fig. 8 On-Resistance Variation with Temperature

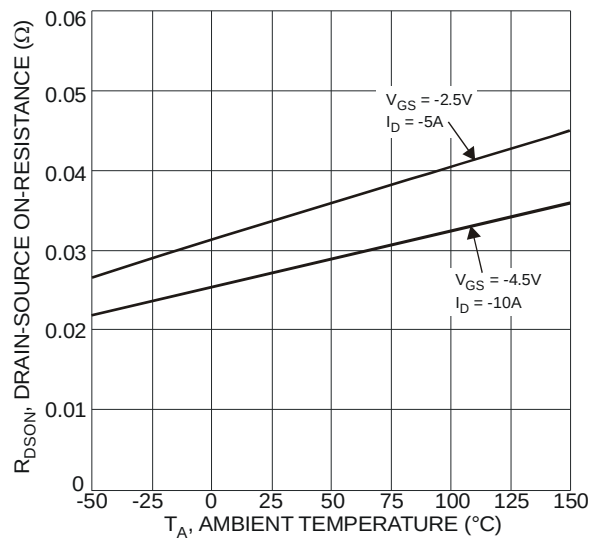


Fig. 9 On-Resistance Variation with Temperature

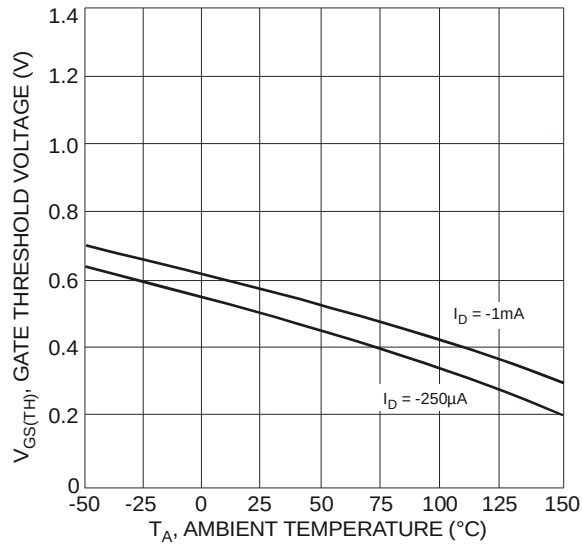


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

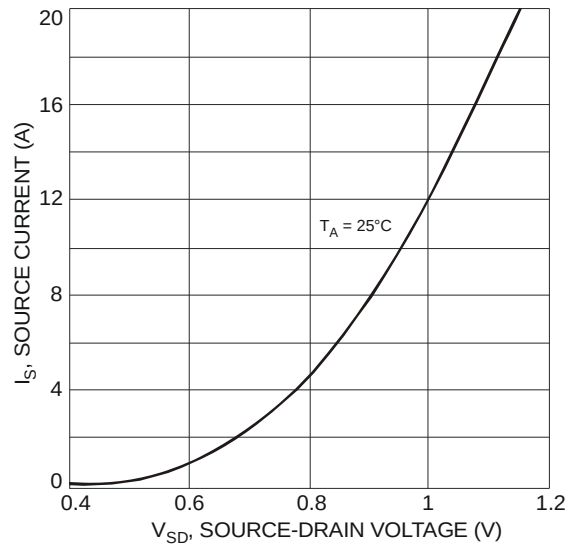


Fig. 11 Diode Forward Voltage vs. Current

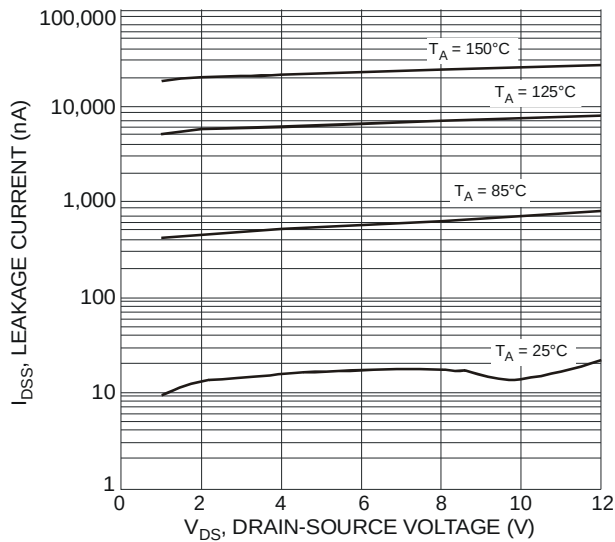


Fig. 12 Typical Drain-Source Leakage Current vs. Voltage

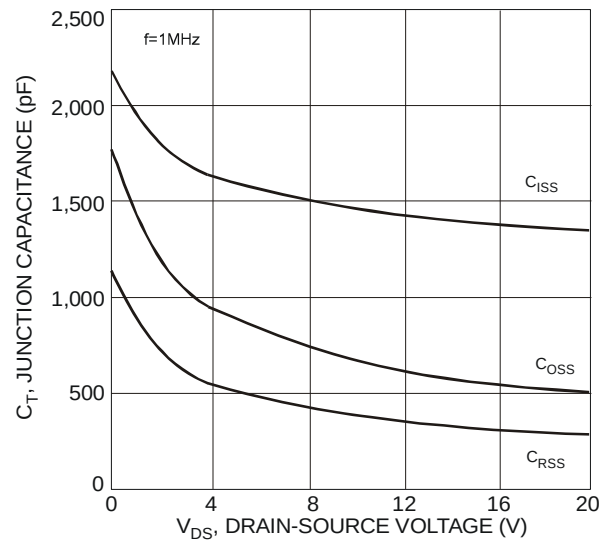


Fig. 13 Typical Junction Capacitance

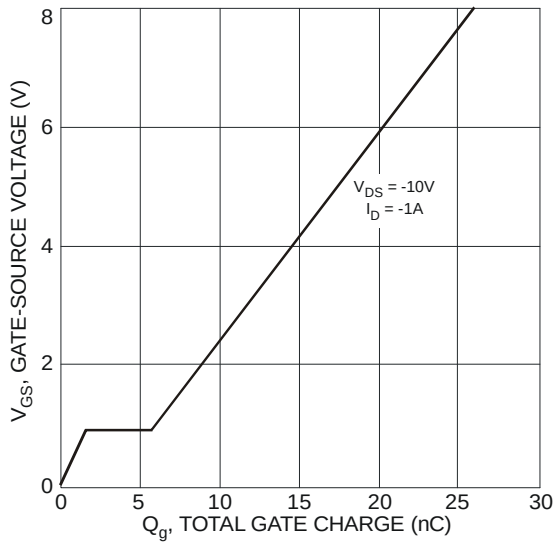
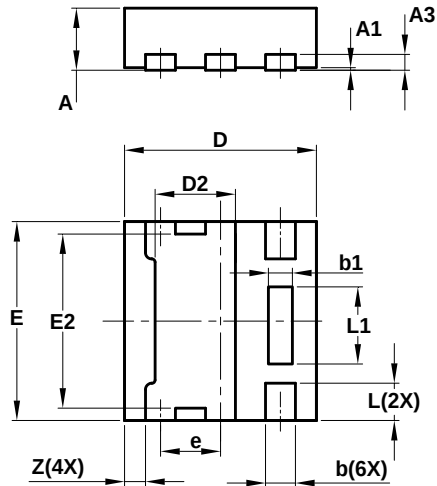


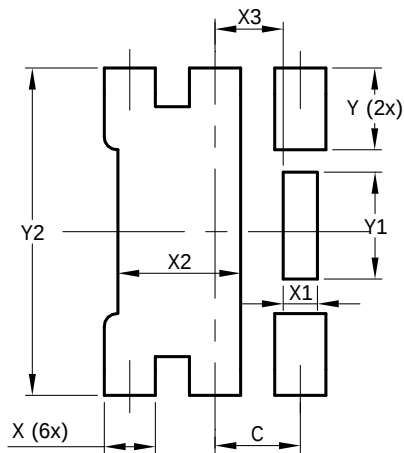
Fig. 14 Gate-Charge Characteristics

Package Outline Dimensions



X1-DFN1616-6 Type E			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
b1	0.10	0.30	0.20
D	1.55	1.65	1.60
D2	0.57	0.77	0.67
E	1.55	1.65	1.60
E2	1.30	1.50	1.40
e	—	—	0.50
L	0.25	0.35	0.30
L1	0.52	0.72	0.62
Z	—	—	0.175
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
C	0.500
X	0.300
X1	0.200
X2	0.720
X3	0.400
Y	0.475
Y1	0.620
Y2	1.900

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9